

# **FLIP CHIP TYPE SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING THE SAME**

## Abstract of the Disclosure

5 A flip chip type semiconductor device comprises at least one first metal line and at least a pair of second metal lines formed in the passivation layer, an aluminum pad covering the first metal line, an aluminum fuse covering the pair of second metal lines adjacent to each other and the passivation layer therebetween, and an under-bump metal layer pattern and a bump formed on the aluminum pad in order. The first and second metal lines are formed respectively in first and second grooves by using a damascene process after forming first and second grooves in the passivation layer.

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